

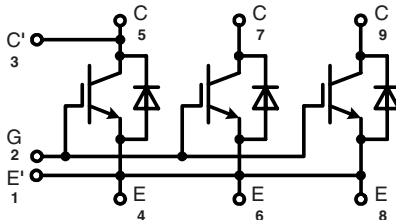
IGBT Module Single switch

Short Circuit SOA Capability
Square RBSOA

$$I_{C80} = 1200 \text{ A}$$

$$V_{CES} = 3300 \text{ V}$$

$$V_{CE(sat) \text{ typ.}} = 3.1 \text{ V}$$



IGBT

Symbol	Conditions	Maximum Ratings	
V_{CES}	$V_{GE} = 0 \text{ V}$	3300	V
V_{GES}		± 20	V
I_{C80}	$T_C = 80^\circ\text{C}$	1200	A
I_{CM}	$t_p = 1 \text{ ms}; T_C = 80^\circ\text{C}$	2400	A
t_{SC}	$V_{CC} = 2500 \text{ V}; V_{CEM \text{ CHIP}} \leq 3300 \text{ V};$ $V_{GE} \leq 15 \text{ V}; T_{VJ} \leq 125^\circ\text{C}$	10	μs

Features

- NPT³ IGBT
 - Low-loss
 - Smooth switching waveforms for good EMC
- Industry standard package
 - High power density
 - AISiC base-plate for high power cycling capacity
 - AlN substrate for low thermal resistance

Typical Applications

- AC power converters for
 - industrial drives
 - windmills
 - traction
- LASER pulse generator

Symbol	Conditions	Characteristic Values ($T_{VJ} = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
$V_{CE(sat)} \text{ ①}$	$I_C = 1200 \text{ A}; V_{GE} = 15 \text{ V}; T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$		3.1 3.8	V V
$V_{GE(th)}$	$I_C = 240 \text{ mA}; V_{CE} = V_{GE}$	6		8 V
I_{CES}	$V_{CE} = 3300 \text{ V}; V_{GE} = 0 \text{ V}; T_{VJ} = 125^\circ\text{C}$			120 mA
I_{GES}	$V_{CE} = 0 \text{ V}; V_{GE} = \pm 20 \text{ V}; T_{VJ} = 125^\circ\text{C}$			500 nA
E_{on}	} Inductive load; $T_{VJ} = 125^\circ\text{C}; V_{GE} = \pm 15 \text{ V};$ $V_{CC} = 1800 \text{ V}; I_C = 1200 \text{ A}; R_G = 1\Omega; L_\sigma = 100 \text{ nH}$		1750	mJ
E_{off}			2000	mJ
R_{thJC}				0.0085 K/W

① Collector emitter saturation voltage is given at chip level

Diode

Symbol	Conditions	Maximum Ratings	
I_{F80}	$T_C = 80^\circ\text{C}$	1200	A
I_{FSM}	$V_R = 0\text{ V}; T_{VJ} = 125^\circ\text{C}; t_p = 10\text{ ms};$ half-sinewave	12000	A

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
V_F ②	$I_F = 1200\text{ A}; T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$	2.30		V
		2.35		V
I_{RM} t_{rr} Q_{RR} E_{rec}	$V_{CC} = 1800\text{ V}; I_C = 1200\text{ A};$ $V_{GE} = \pm 15\text{ V}; R_G = 1\ \Omega; T_{VJ} = 125^\circ\text{C}$ Inductive load; $L_\sigma = 100\text{ nH}$	1680		A
		800		ns
		1320		μC
		1740		mJ
R_{thJC}				0.017 K/W

② Forward voltage is given at chip level

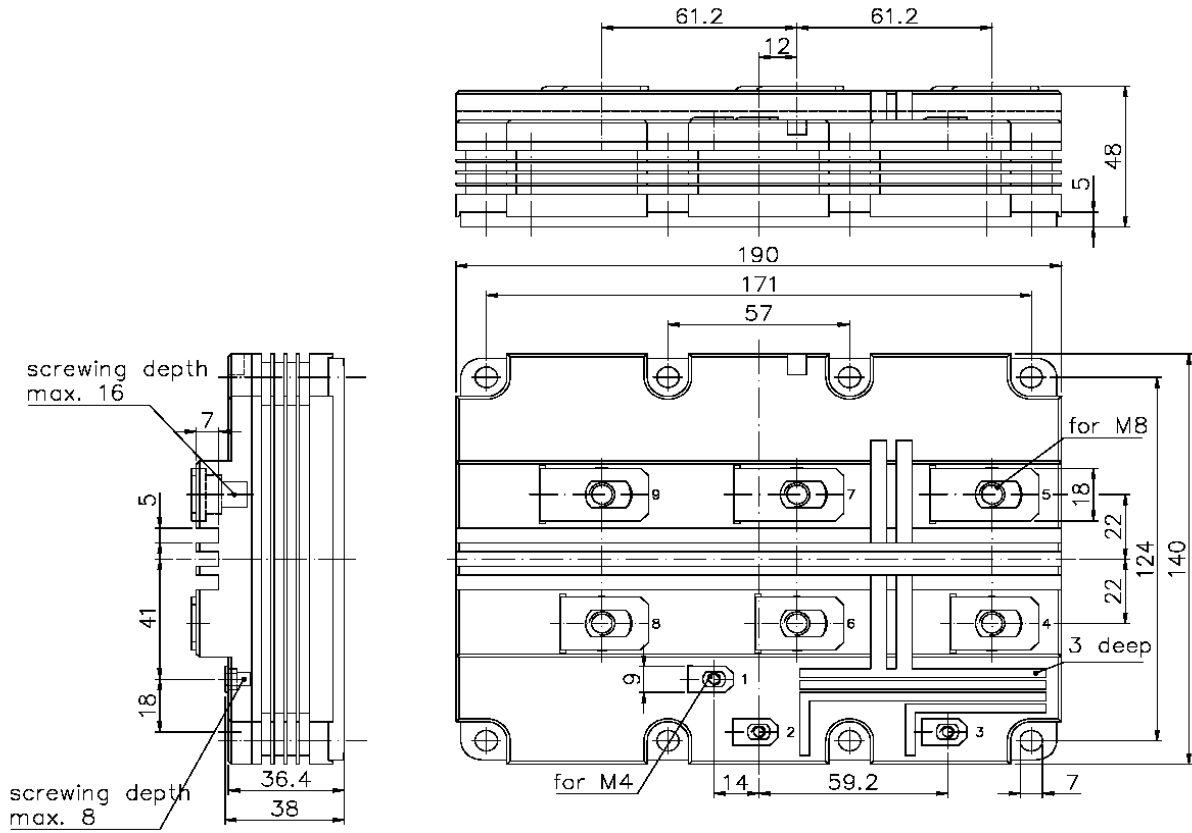
Module

Symbol	Conditions	Maximum Ratings	
T_{JM}	max junction temperature	+125	$^\circ\text{C}$
T_{VJ}	Operating temperature	-40...+125	$^\circ\text{C}$
T_{stg}	Storage temperature	-40...+125	$^\circ\text{C}$
M_d	Mounting torque	Base-heatsink, M6 screws	4 - 6 Nm
		Main terminals, M8 screws	8 - 10 Nm

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
d_A	Clearance distance	terminal to base	26	mm
		terminal to terminal	26	mm
d_s	Surface creepage distance	terminal to base	56	mm
		terminal to terminal	56	mm
V_{ISOL}	1 min, $f = 50\text{ Hz}$	10500		V~
V_E	Partial discharge extinction voltage $f = 50\text{ Hz}, Q_{PD} \leq 10\text{ pC}$	5100		V
CTI	Comperative tracking index	600		
L_σ	Module stray inductance, C to E terminal		18	nH
$R_{term-chip}^*$	Resistance terminal to chip		0.12	m Ω
R_{thCH}	per module; λ grease = 1 W/m \cdot K		0.006	K/W
Weight			1500	g

*) $V = V_{CE(sat)} + R_{term-chip} \cdot I_C$ resp. $V = V_F + R_{term-chip} \cdot I_F$

Outline drawing



Note: all dimensions are shown in mm